

A cross-sectional view of a semiconductor device. A gate stack 101 is formed on a substrate. The gate stack 101 includes a gate electrode 106 and a gate insulating layer 301. The gate insulating layer 301 is located between the gate electrode 106 and the substrate.

FIG.3

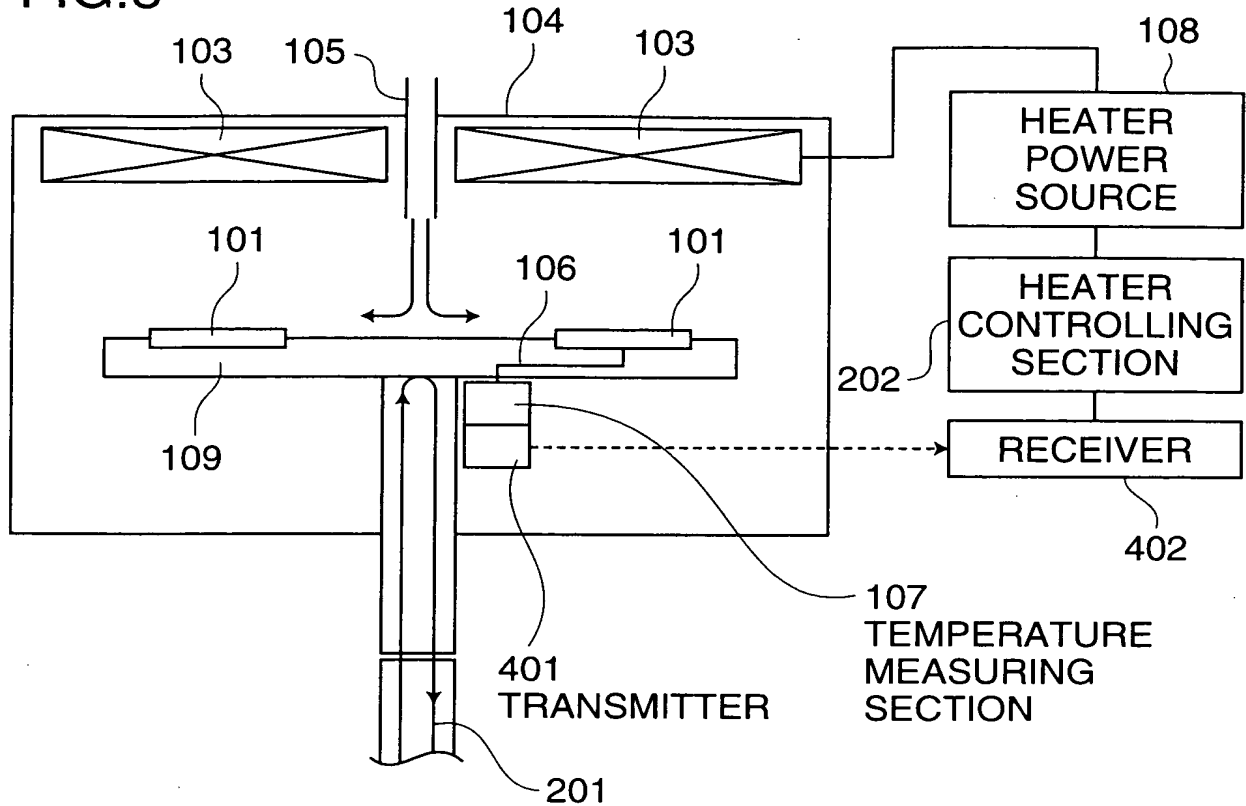


FIG.4

